STRAINED SILICON MOSFET HAVING IMPROVED CARRIER MOBILITY, STRAINED...
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Sheet 1 of 1

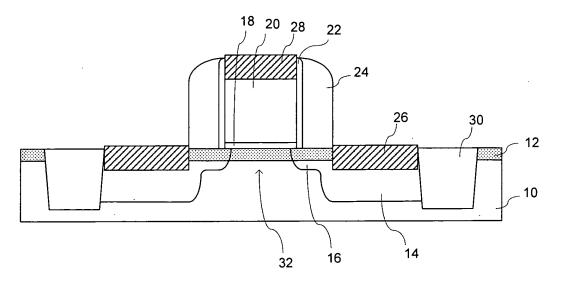
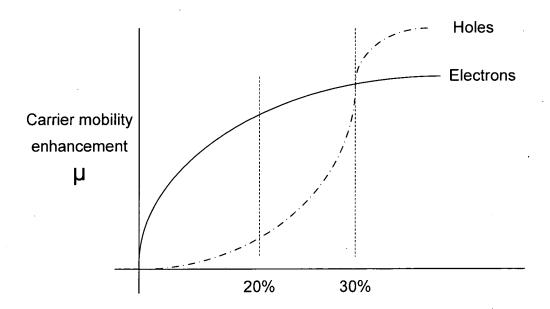


Figure 1 **Prior Art**



Si_{1-x}Ge_x germanium content

Figure 2 **Prior Art**